

**CMOSH-4E**

**ENHANCED SPECIFICATION  
SURFACE MOUNT  
SILICON SCHOTTKY DIODE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMOSH-4E is an Enhanced version of the CMOSH-3 Silicon Schottky Diode in an SOD-523 Surface Mount Package.

**MARKING CODE: 4E**

**ENHANCED SPECIFICATIONS:**

- ◆  $I_F$  from 100mA max to 200mA max.
- ◆  $BV_R$  from 30V min to 40Vmin.
- ◆  $V_F$  from 1.0V max to 0.8V max.

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

- ◆ **Peak Repetitive Reverse Voltage**
- ◆ **Continuous Forward Current**  
Peak Repetitive Forward Current  
Peak Forward Surge Current,  $t_p=10\text{ms}$   
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

SYMBOL	UNITS
$V_{RRM}$	40 V
$I_F$	200 mA
$I_{FRM}$	350 mA
$I_{FSM}$	750 mA
$P_D$	250 mW
$T_J, T_{stg}$	-65 to +150 °C
$\theta_{JA}$	500 °C/W

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

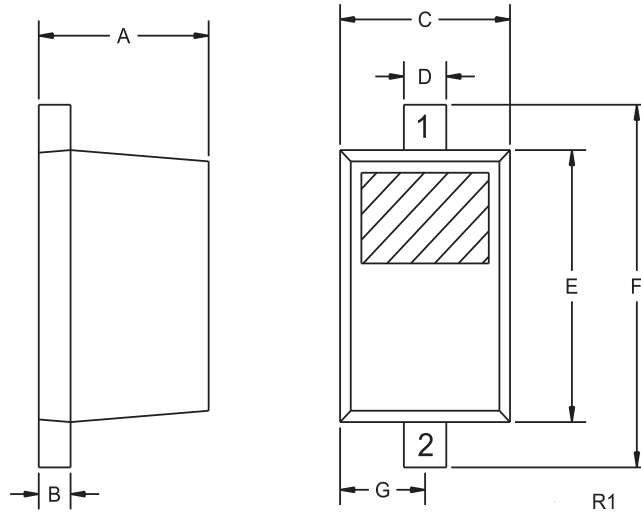
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
◆ $BV_R$	$I_R=100\mu\text{A}$	40	50		V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
◆ $V_F$	$I_F=15\text{mA}$		0.37	0.42	V
◆ $V_F$	$I_F=100\text{mA}$		0.61	0.80	V
◆ $V_F$	$I_F=200\text{mA}$		0.65	1.0	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

- ◆ Enhanced specification.
- ◆◆ Additional Enhanced specification.

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**SOD-523 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Cathode
- 2) Anode

**MARKING CODE: 4E**

<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)

R2 (25-January 2010)